

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0032] of the specification with the following amended paragraph:

[0032] Gate dielectric **110** can be formed on a surface of substrate **100** utilizing any conventional deposition process including, for example, chemical vapor deposition (CVD), plasma-assisted CVD, plasma assisted oxidation, thermal deposition, atomic layer CVD, evaporation, sputtering, remote plasma nitridization (RPN), and chemical solution deposition. Gate dielectric **110** is not limited to any particular material may comprise any number of materials, or combinations of materials, suitable for use as a gate dielectric. For example, gate dielectric **110** may comprise any conventional dielectric material such as, ~~such as;~~ for example, silicon oxides, silicon nitrides, silicon oxynitrides and mixtures, alloys, or multilayers thereof. It may also comprise a high-k material such as, for example, HfO_2 , ZrO_2 , HfSiO_2 , ZrSiO_2 , AlSi , and mixtures, alloys, or multilayers thereof. A preferred material for the gate dielectric is SiO_2 .